

*Amendments to the Claims*

The listing of claims will replace all prior versions, and listings of claims in the application.

Claims 1-12. (Cancelled)

Claim 13. (Currently amended) A semiconductor light emitting device comprising:

an electrode;

a substrate;

gallium nitride type compound semiconductor layers forming a light emitting portion, said semiconductor layers including at least an n-type layer and a p-type layer, a band gap energy of the p-type layer being greater than a band gap energy of the n-type layer, said semiconductor layers being between said electrode and said substrate; and

a buffer region interposed between said substrate and said semiconductor layers, said buffer region alleviating strain resulting from a lattice mismatch between said substrate and said semiconductor layers, wherein said buffer region comprises a first layer, said first layer including In.

Claim 14. (Previously Presented) The semiconductor light emitting device according to claim 13, wherein said buffer region includes a second layer formed at a first temperature on said substrate, and wherein said first layer includes the elements In, Ga, and N, said first layer being formed at a second temperature higher than said first temperature.

Claim 15. (Cancelled)

Claim 16. (Previously Presented) The semiconductor light emitting device according to claim 14, wherein the conductivity of the first layer is greater than the conductivity of the second layer.

Claim 17. (Cancelled)

Claim 18. (Previously Presented) The semiconductor light emitting device according to claim 16, wherein the second layer consists of a semiconductor layer of high resistance.

Claim 19. (Cancelled)

Claim 20. (Previously Presented) The semiconductor light emitting device according to claim 13, wherein said buffer region further comprises a second layer formed at a first temperature on the surface of said substrate, wherein said first layer is formed at a second temperature higher than said first temperature, said first layer being between said second layer and said semiconductor layers, said light emitting device further including a p-type contact layer between said semiconductor layers and said electrode.

Claim 21. (Previously Presented) The semiconductor light emitting device according to claim 20, wherein said p-type contact layer consists of essentially GaN.

Claims 22-52. (Cancelled)

Claims 53. (Original) The semiconductor light emitting device according to claim 13, wherein said buffer region further comprises a second layer formed at a first temperature on the surface of said substrate, wherein said first layer includes the elements In, Ga, and N, and said first layer is formed at a second temperature higher than said first temperature, said first layer being between said second layer and said semiconductor layers, said light emitting device further including a p-type contact layer between said semiconductor layers and said electrode.